SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 21 with:

For example, the semiconductor laser device described above has a construction as follows. That is, on a substrate composed of n-type (referred to as "n-" hereinafter) GaAs, there are provided, by turns, a lower clad layer composed of n-AlGaInP, an active layer having a multiple quantum well structure, a first upper clad layer composed of p-type (referred to as "p-" hereinafter) AlGaInP, an etching stopper layer (sometimes referred to as "ESL" hereinafter) with a multiple quantum well structure composed of p-AlGaInP and GaInP, a second upper clad layer composed of p-AlGaInP and having a stripe-form protrusion, a contact layer composed of p-GaAs, and a p-electrode (for example, see Japanese laid-open patent publication No. Hei 10-125995 (paragraph [0016] and Fig. 1)). The top surface of the second upper clad layer is covered with an insulative film except the portion corresponding to the stripe-form protrusion.

Replace the paragraph beginning at page 2, line 12 with:

Meanwhile, because ~~in~~ the conventional semiconductor laser device, for example described in the above-mentioned publication, ~~it is provided with~~ includes the etching stopper layer with the multiple quantum well structure composed of p-AlGaInP and GaInP, ~~it occurs such a problem that its~~ luminous efficiency is lowered. According to knowledge of the present inventors, it is assumed that the luminous efficiency is lowered by about 7% in the event that the etching stopper layer is provided, as compared to the case in which no etching stopper layer is provided (see Fig. 10 discussed later).

Replace the paragraph beginning at page 3, line 7 with:

In general, ~~the~~ light absorption at the contact layer composed of p-GaAs can be prevented or suppressed, if the thickness of the second upper clad layer composed of p-AlGaInP is increased to prevent the light distribution from reaching the contact layer. ~~However, in~~ In an index guide laser provided with a light-guiding ~~mechanism which encloses~~ structure, a laser beam ~~by~~ is confined due to the difference of refractive indexes between the second upper clad layer composed of p-AlGaInP with the stripe-form protrusion and the layers on ~~its~~ both sides, ~~if~~ at the second upper clad layer. If a clad layer composed of a material with high resistivity is used, ~~there occurs such a problem that~~ the resistance of the

stripe-form protrusion is increased and the output characteristics or temperature characteristics at the time of high output may be deteriorated.

Replace the paragraph beginning at page 5, line 20 with:

Fig. 1 is a perspective view of a semiconductor laser device according to Embodiment 1 of the present invention, which is partly cut ~~off~~ away;